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IN THE CLAIMS:

Please cancel all claims from the application and replace by the following new claims:

12. A method of manufacturing a semiconductor device, comprising the steps of:

- forming first and second gate electrodes of first and second transistors on a main surface of a semiconductor substrate with a space between each other;
- forming a nitride film covering said first and second gate electrodes;
- forming source/drains of said first and second transistors;
- forming an interlayer insulating film covering said nitride film;
- forming in said interlayer insulating film a first contact hole reaching one of said source/drain of said first transistor;
- providing a second contact hole formed in said interlayer insulating film and reaching said source/drain of said second transistor and a third contact hole penetrating said interlayer insulating film and said nitride film reaching said second gate electrode; and
- forming a bit line connected via said first contact hole to one of said source/drain of said

~~first transistor, and first and second interconnections extending in said second and third contact holes.~~

¹²
~~13.~~ The method according to claim 12, said source/drain of said second transistor having a highly doped region, wherein:

the step of forming said source/drain of said second transistor includes the step of forming first metal silicide at a surface of said heavily doped region; and

the step of forming said bit line includes the steps of: forming a plug electrode in said first contact hole; forming second metal silicide at a surface of said plug electrode; and forming said bit line on said second metal silicide.

¹³
~~14.~~ A method of manufacturing a semiconductor device, comprising the steps of:
forming first and second gate electrodes of first and second transistors on a main surface of a semiconductor substrate with a space between each other;

forming a nitride film covering side walls of said first and second gate electrodes;

forming first impurity regions at opposite sides of said first and second gate electrodes;

forming an interlayer insulating film covering said first and second gate electrodes;

forming in said interlayer insulating film a contact hole reaching one of said first impurity regions of said first transistor and said nitride film;

introducing impurity into said semiconductor substrate through said contact hole to form a second impurity region overlapping with said one of said first impurity regions of said first